

In the Claims

1. (Currently Amended) An organic electroluminescent device comprising:
a substrate;
a thin film transistor formed on the substrate;
a first electrode electrically coupled to the thin film transistor formed on the substrate;
a chemical vapor deposition CVD insulating film having of a low dielectric constant formed on the first electrode and the substrate, the chemical vapor deposition CVD film having an opening portion for exposing the first electrode;
an organic electroluminescent (EL) layer formed on a base and a sidewall of the opening portion without filling the opening; and
a second electrode formed on the organic electroluminescent EL layer.
2. (Currently Amended) The device as claimed in claim 1, wherein the chemical vapor deposition CVD insulating film comprises is comprised of SiOC.
3. (Currently Amended) The device as claimed in claim 1, wherein the chemical vapor deposition CVD insulating film has a dielectric constant less than about 3.5.
4. (Currently Amended) The device as claimed in claim 1, wherein the chemical vapor deposition CVD insulating film is formed to have a thickness more than about 1 μm .
5. (Currently Amended) An The organic electroluminescent device comprising:
a substrate;
a thin film transistor formed on the substrate and having an active pattern, a gate insulating film, a gate electrode, and source/drain electrodes;
a passivation layer formed on the thin film transistor and the substrate;
a pixel electrode formed on the passivation layer so as to be connected with the thin film transistor;
a chemical vapor deposition CVD insulating film having of a low dielectric constant

formed on the pixel electrode and the passivation layer, the chemical vapor deposition CVD insulating film having an opening portion for exposing the pixel electrode;

an organic electroluminescent EL layer formed on a base and a sidewall of the opening portion without filling the opening portion; and

a metal electrode formed on the organic electroluminescent EL layer and the chemical vapor deposition CVD insulating film having of a low dielectric constant.

6. (Currently Amended) The device as claimed in claim 5, wherein the chemical vapor deposition CVD insulating film comprises is comprised of SiOC.

7. (Currently Amended) The device as claimed in claim 5, wherein the chemical vapor deposition CVD insulating film has a dielectric constant less than about 3.5.

8. (Currently Amended) The device as claimed in claim 5, wherein the chemical vapor deposition CVD insulating film has a thickness more than about 1 μ m.

9. (Currently Amended) The device as claimed in claim 5, wherein the chemical vapor deposition CVD insulating film and an edge portion of the pixel electrode overlap each other in a width by more than about 1 μ m.

10. (Currently Amended) An organic electroluminescent device comprising:
a substrate;
a thin film transistor formed on the substrate;
a stripe-shaped first electrode electrically coupled to the thin film transistor formed on the substrate;
a chemical vapor deposition CVD insulating film having of a low dielectric constant formed on the first electrode and the substrate, the chemical vapor deposition CVD insulating film having an opening portion formed on the first electrode with a tapered shape;
an organic electroluminescent (EL) layer formed on the opening portion; and
a stripe-shaped second electrode formed on the organic electroluminescent EL layer, the stripe-shaped second electrode being arranged to cross the first electrode.

11. (Currently Amended) The device as claimed in claim 10, wherein the chemical vapor deposition CVD insulating film is comprised of SiOC.

12. (Currently Amended) The device as claimed in claim 10, wherein the chemical vapor deposition CVD insulating film has a dielectric constant less than about 3.5.

13. (Currently Amended) The device as claimed in claim 10, wherein the chemical vapor deposition CVD insulating film has a thickness more than about 1 μm .